

**Amendments to the Specification**

Page 1, lines 5-9, please amend this paragraph to read as follows:

This application is based upon and claims the benefit of priority under 37 CFR §119 from the prior Japanese Patent Applications No. 2000-094574, filed March 30, 2000; and under 37 CFR §120 from U.S. Application Serial No. 10/375,084, filed February 28, 2003, which is a divisional application of U.S. Patent No. 6,555,851, which issued April 29, 2003, entire contents of which are incorporated herein by reference.

Page 9, lines 13-27, please amend this paragraph to read as follows:

FIG. 4 is a schematic cross-sectional view of a high electron mobility transistor (HEMT) according to a first embodiment of the present invention. Reference numerals 11, 12, 13, 14[[[,] and 15 denote a GaN electron accumulation layer,  $\text{Al}_x\text{Ga}_{(1-x)}\text{N}$  spacer layer, n-type  $\text{Al}_x\text{Ga}_{(1-x)}\text{N}$  electron supply layer,  $\text{Al}_x\text{Ga}_{(1-x)}\text{N}$  cap layer, and sapphire substrate, respectively. A gate electrode 16 is formed on the cap layer 14, while a source electrode 17 and a drain electrode 18 are formed on the electron supply layer 13. Furthermore, a hole absorption electrode 19 is formed for absorbing holes in a recess portion 24. The recess portion 24 is formed for isolation by removing a peripheral [[potion]] portion, other than an element region, of layers 12, 13 and 14 to reach the electron accumulation layer 11.